

Description

JMT N-channel MOSFET

Features

- $V_{DS}=30V$, $I_D=5.8A$
- $R_{DS(ON)} < 25m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 40m\Omega$ @ $V_{GS} = 4.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

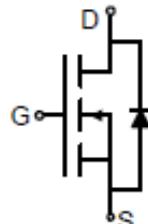
Application

- PWM Applications
- Load Switch
- Power Management

Package



SOT-23



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	5.8	A
		$T_c = 100^\circ C$	4	
I_{DM}	Pulsed Drain Current ^{note1}		30	A
P_D	Power Dissipation	$T_A = 25^\circ C$	1.5	W
R_{eJA}	Thermal Resistance, Junction to Ambient		85	$^\circ C/W$
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ C$

**Electrical Characteristics** ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	1.5	2.5	V
$R_{DS(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{GS}=10\text{V}, I_D=5\text{A}$	-	18	25	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=4\text{A}$	-	28	40	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=5\text{A}$	3	5.8	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	560	-	pF
C_{oss}	Output Capacitance		-	125	-	pF
C_{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q_g	Total Gate Charge	$V_{DS}=10\text{V}, I_D=3.6\text{A}, V_{GS}=5\text{V}$	-	7	-	nC
Q_{gs}	Gate-Source Charge		-	1.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=15\text{V}, I_D=5.5\text{A}, R_{GEN}=2.5\Omega, V_{GS}=10\text{V}$	-	10	-	ns
t_r	Turn-on Rise Time		-	4	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	27	-	ns
t_f	Turn-off Fall Time		-	5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current	-	-	5.8	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	30	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_s=1.7\text{A}$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure1: Output Characteristics

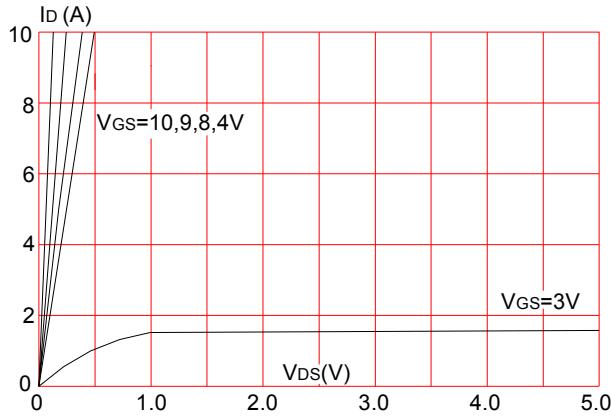


Figure 3: On-resistance vs. Drain Current

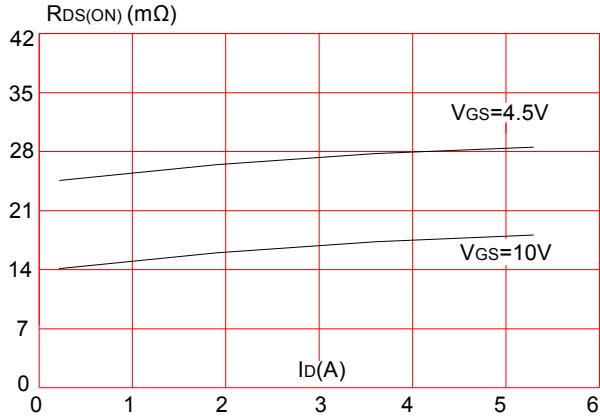


Figure 5: Gate Charge Characteristics

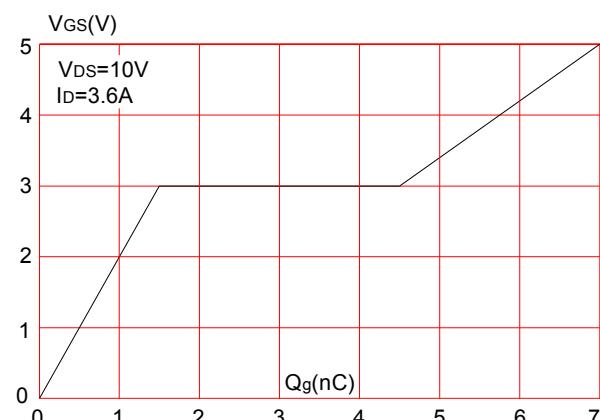


Figure 2: Typical Transfer Characteristics

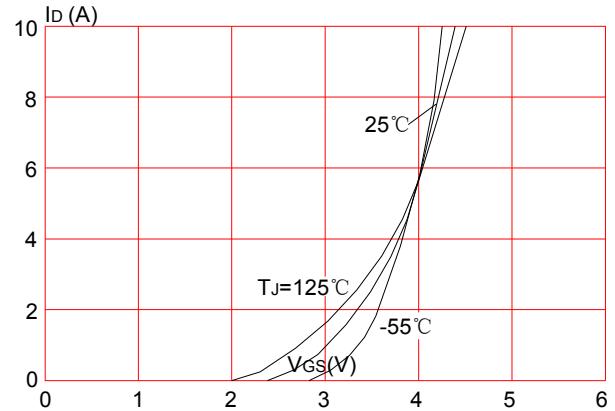


Figure 4: Body Diode Characteristics

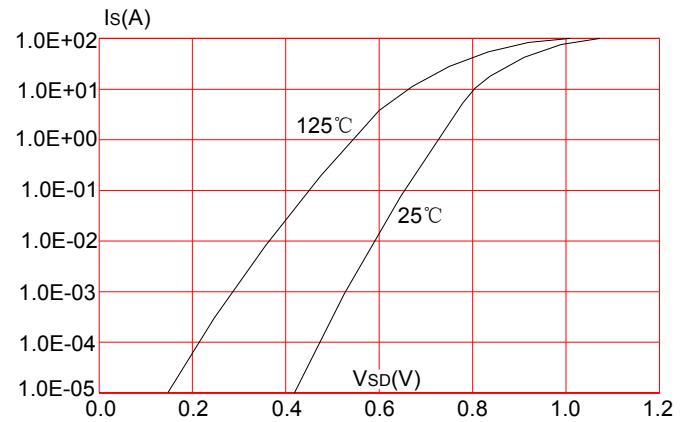


Figure 6: Capacitance Characteristics

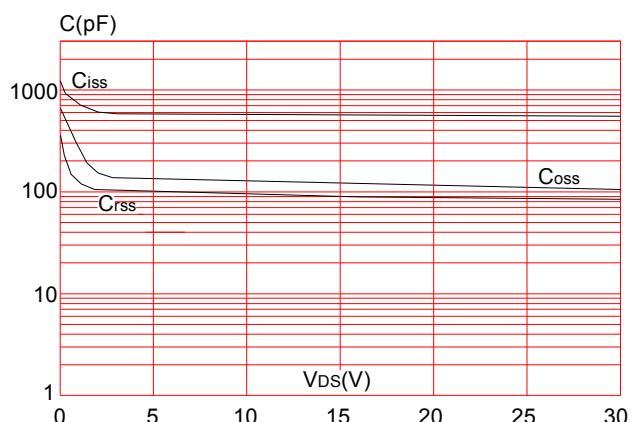


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

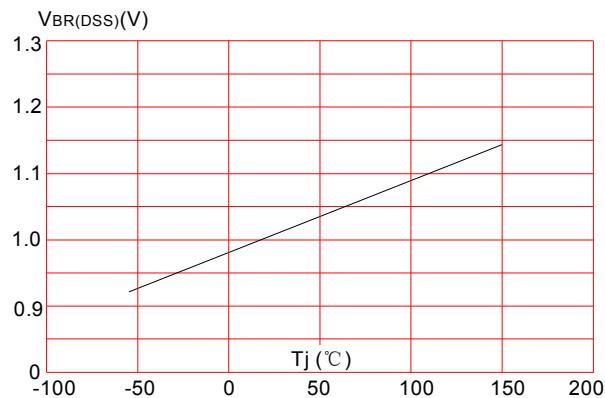


Figure 9: Maximum Safe Operating Area

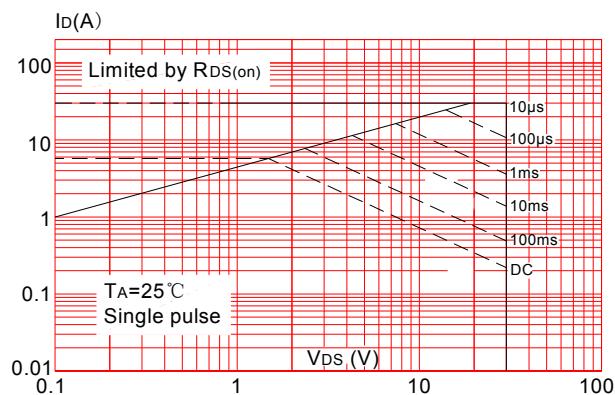


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (SOT-23)

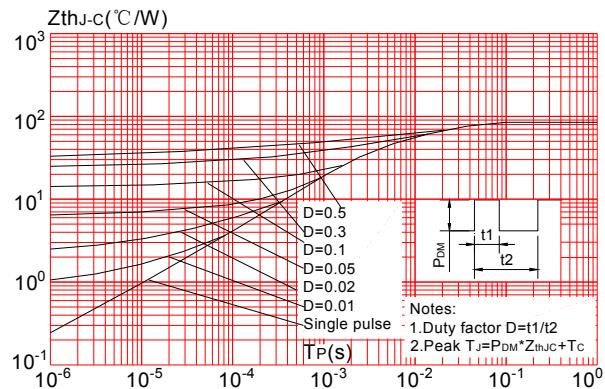


Figure 8: Normalized on Resistance vs. Junction Temperature

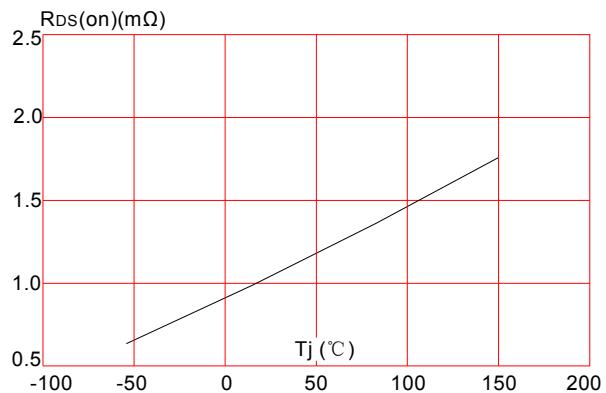
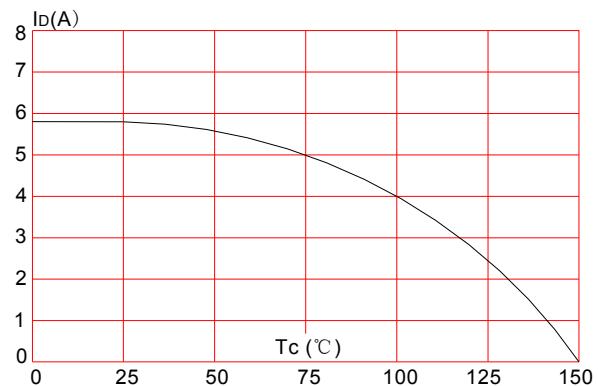


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



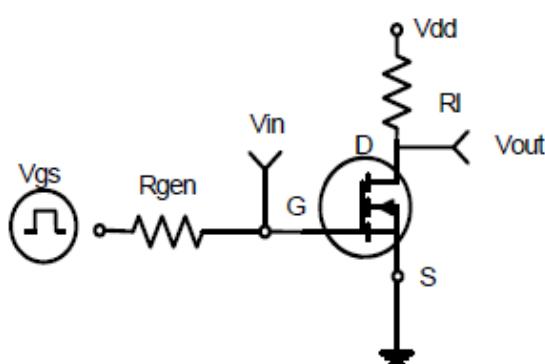


Figure1:Switching Test Circuit

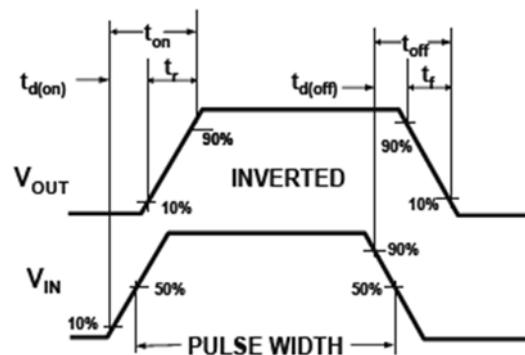
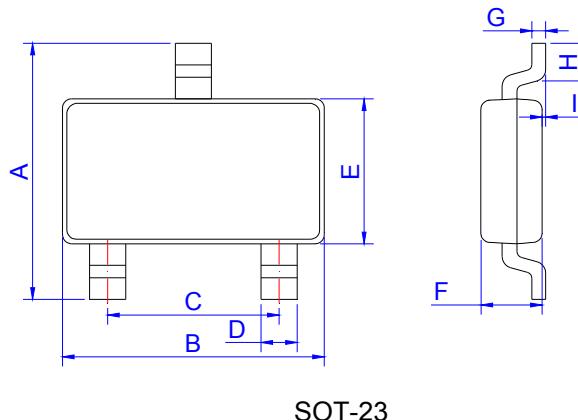


Figure2:Switching Waveforms

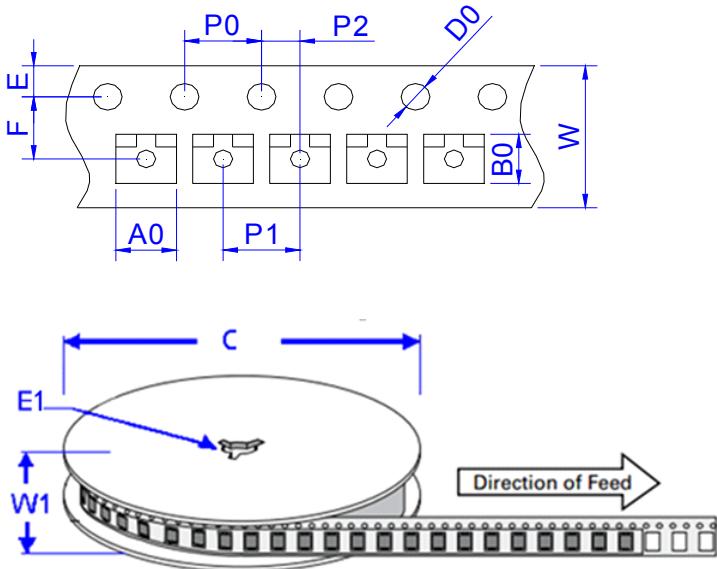
Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004



Reel Specification-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

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